Preface

Sponsors

Dielectrics in microelectronics - problems and perspectives p. 1
Buried oxides: where we have been and where we are going p. 10
RTP - temperature monitoring by means of oxidation p. 23
Low-temperature voltage enhanced UV-assisted oxidation of silicon p. 29
Rapid thermal annealing of SiO[subscript 2] for VLSI applications p. 35
A synchrotron Si2p and As3d core level study of the As-terminated Si(0 0 1) surface oxidation p. 40
Oxidation of amorphous and crystalline silicon p. 45
Fluorinated interlayer dielectric films in ULSI multilevel interconnections p. 49
Deposition of ultra-thin oxide dielectrics for MOSFETs by a combination of low-temperature plasma-assisted oxidation, and intermediate and high-temperature rapid thermal processing p. 60
New substances for atomic-layer deposition of silicon dioxide p. 66
Dual-mode radio frequency / microwave plasma deposition of amorphous silicon oxide thin films p. 70
Hydrogen incorporation in silicon oxide films deposited by ArF laser-induced chemical vapor deposition p. 75
Effects of plasma treatment on the properties of room-temperature liquid-phase deposited (LPD) oxide films p. 81
Oxygen-rich phase segregation in PECVD a-SiO[subscript x]: H semi-insulators p. 86
IR study of short-range and local order in SiO[subscript 2] and SiO[subscript x] films p. 91
Comparison of experimental and calculated TO and LO oxygen vibrational modes in thin SiO[subscript 2] films p. 96
Structural damage and defects created in SiO[subscript 2] films by Ar ion implantation p. 101
Boron diffusion in SiO[subscript 2] based dielectric thin layers p. 106
Formation of visible photoluminescence bands in Si[superscript +]-implanted silica glasses and thermal oxide films on crystalline Si p. 112
Parameters controlling the generation of natural intrinsic EX defects in thermal SiO[subscript 2] on Si p. 119
Wavelength resolved thermally stimulated luminescence of SiO[subscript 2] films p. 124
A novel ellipsometric set up for high precision thin films measurements p. 129
Effects of iron contamination in silicon on thin oxide breakdown and reliability characteristics p. 134
Instability of charged defects in electrically stressed metal-tunnel oxide - silicon diodes p. 140
Influence of FN electron injections in dry and dry/wet/dry gate oxides: relation with failure p. 144
Investigation on the interfacial reaction of [actual symbol not reproducible] system p. 149
Influence of WSi[subscript 2] polysilicide gate process on integrity and reliability of gate and tunnel oxides p. 156
Modeling and simulation of homogeneous degradation for N-channel MOSFETS p. 160
Interface traps induced by hole trapping in metal-oxide semiconductor devices p. 165
Comparison of X-ray-induced electron and hole trapping in various materials (YSZ, SIMOX, thermal SiO$_2$) p. 170

Influence of the oxide charge build-up during Fowler-Nordheim stress on the current-voltage characteristics of metal-oxide-semiconductor capacitors p. 175

Comparison of the generated oxide charge by injection of electrons for both polarities p. 181

Field mechanism of defect generation at Si-SiO$_2$ interface under hot electron injection p. 186

Comparison of rapid ramp voltage and tunnelling injection stress experiments for the characterization of thin MOS gate oxides p. 190

Leakage current reduction due to hot carrier effects in n-channel polycrystalline silicon thin film transistors p. 195

Enhanced MOS 1/f noise due to near-interfacial oxygen deficiency p. 199

The microscopic nature of donor-type Si-SiO$_2$ interface states p. 206

Three-level charge pumping study of radiation-induced defects at Si-SiO$_2$ interface in submicrometer MOS transistors p. 211

The no-thermal activation of the defect generation mechanism in a MOS structure p. 216

A study comparing measurements of roughness of silicon and SiO$_2$ surfaces and interfaces using scanning probe microscopy and neutron reflectivity p. 221

Characterization of ion-implanted silicon-insulator interfaces by reflected optical second harmonic generation p. 227

Dissociation of H$_2$ at silicon dangling orbitals in a-SiO$_2$: a quantum mechanical treatment of nuclear motion p. 232

Atomic hydrogen-induced degradation of thin SiO$_2$ gate oxides p. 244

The role of hydrogen in the action of fluorine in Si/SiO$_2$ structures p. 248

Hydrogen-annealing induced positive charge in buried oxides: correspondence between ESR and C-V results p. 253

Chemical reactions of hydrogenous species in the Si/SiO$_2$ system p. 257

Measurement and analysis of hydrogen depth profiles in MOS-structures by using the $^{15}$N nuclear reaction method p. 264

Electrical properties of hydrogen-rich Si/SiO$_2$ structures p. 270

Surface potential dependence of interface state passivation in metal-tunnel oxide-silicon diodes p. 273

Structural and bonding properties of amorphous silicon nitride films p. 278

A comparative study on structural and electronic properties of PECVD a-SiO$_2$ with a-SiN$_x$ p. 287

The effect of hydrogen and temperature on the optical gaps of silicon nitride and comparative stoichiometry studies on SiN thin films p. 291

Nature of the Si and N dangling bonds in silicon nitride p. 297

Morphology of LPCVD Si$_3$N$_4$ films after high temperature treatment and HF etching p. 301

Hydrogen content of amorphous PECVD SiN$_x$: H films by infrared spectroscopy and hydrogen forward scattering results p. 308

Bias stress studies of a-SiN : H/a-Si : H MIS structures from quasistatic capacitance measurements p. 313
Selective thermal - as opposed to non-selective plasma - nitridation of Si-Ge related materials examined by in situ photoemission techniques p. 319

Influence of gas residence time on the deposition of nitrogen-rich amorphous silicon nitride p. 324

Influence of the deposition parameters on the bonding and optical properties of SiN[subscript x] ECR films p. 329

Room-temperature deposition of SiN[subscript x] using ECR-PECVD for III/V semiconductor microelectronics in lift-off technique p. 334

Control of bonded-hydrogen in plasma-deposited silicon nitrides: Combined plasma-assisted deposition and rapid thermal annealing for the formation of device-quality nitride layers for applications in multilayer dielectrics p. 340

Plasma-enhanced silicon nitride deposition for thin film transistor applications p. 347

Deposition of amorphous silicon nitride thin films by CO[subscript 2] laser-induced chemical vapour deposition p. 353

Structural and electrical properties of thin SiO[subscript 2] layers grown by RTP in a mixture of N[subscript 2][O and O[subscript 2]] p. 361

Damage induced by carrier injection in 8 nm thick oxides and nitrided oxides p. 365

Characterization of thin nitrided oxide layers using high spatial resolution electron energy loss spectrometry p. 369

A comparison of Si-SiO[subscript 2] interface trap properties in thin-film transistors with thermal and plasma nitrided oxides p. 374

Structural and optical properties of nitrided silicon oxide layers rapidly thermally grown in a pure N[subscript x]O ambient p. 380

Structural identification of point defects in amorphous silicon oxynitrides p. 385

Silicon oxynitride study by the tetrahedron model and by spectroscopic ellipsometry p. 395

Effect of process parameters on the properties of electron cyclotron resonance plasma deposited silicon-oxynitride p. 403

Electrical properties of Au/Bn/InP MIS diodes p. 409

Surface plasmon-induced luminescence: a probe to study electrical aging and dielectric breakdown in polymer-like thin films p. 415

Structure rearrangement and electrochromic properties of amorphous tungsten trioxide films p. 420

Low pressure chemical vapour deposition of tantalum pentoxide thin layers p. 425

Investigation of the film growth of a new titanium precursor for MOCVD p. 430

Low temperature deposition of gallium phosphate amorphous dielectric thin films by aerosol CVD p. 435

Fabrication, characterization and electro-optic performances of proton-implanted waveguides in LiNbO[subscript 3] p. 443

Photo-assisted switching and trapping in BaTiO[subscript 3] and Pb(Zr, Ti)O[subscript 3] ferroelectrics p. 448

Optical properties of sol - gel derived ferroelectric films p. 453

Chemical interaction in ion-implanted amorphous SiO[subscript 2] and application to formation and modification of nanosize colloid particles p. 457

Light-assisted deposition of silicon-based dielectrics for optical interconnection in optoelectronics p. 473

PECVD a-SiN[subscript x]: H films for dielectric insulation in buried ridge structure p. 477

Fabry-Perot and distributed feedback laser devices
Properties and applications of electron cyclotron plasma deposited SiO$_x$N$_y$ films with graded refractive index profiles  p. 484
Light-modulated carrier injection across the interface between transparent conducting oxide (n$^{+}$-SnO$_2$) and semi-insulating amorphous silicon-carbide  p. 489
Thermo-optic mode extinction modulation in polymeric waveguide structures  p. 494
Author index  p. 499
Subject index  p. 505
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